

2N5879-2N5880 - PNP 2N5881-2N5882 - NPN

COMPLEMENTARY SILICON POWER TRANSISTORS

FEATURES:

- Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number
- Available Non-RoHS (standard) or RoHS compliant (add PBF suffix)

MAXIMUM RATINGS

		2N5879	2N5880		
Ratings	Symbol	2N5881	2N5882	Unit	
Collector-Emitter Voltage	V _{CEO}	60	80	V	
Collector-Base Voltage	V _{CBO}	60	80	V	
Emitter-Base Voltage	V _{EBO}	5		V	
Collector Current -Continuous	l _o	I _C 15 30		А	
Peak	10				
Base Current	I _B	5.0		А	
Total Power Dissipation	P _D	160 0.915		W	
Derate above 25°C	PD			W/°C	
Operating and Storage Temperature Range	$T_{J_{i}}T_{STG}$	-65 to +200		°C	
Thermal Resistance Junction to Case	$R_{\theta JC}$	1.1 °0		°C/W	

ELECTRICAL CHARACTERISTICS @ 25°C unless otherwise noted

Characteristics		Symbol	Min	Max	Unit
Collector Emitter Sustaining Voltage					
I _C = 200mA, I _B = 0	2N5879, 2N5881	$V_{CEO(sus)}$	60	-	V
	2N5880, 2N5882		80	-	
Collector Cutoff Current					
V _{CE} = 30V, I _B = 0	2N5879, 2N5881	I _{CEO}	-	1.0	mA
	2N5880, 2N5882		-	1.0	
Collector Cutoff Current					
V _{CE} = 60V, V _{BE(off)} = 1.5V	2N5879, 2N5881		-	0.5	
V _{CE} = 80V, V _{BE(off)} = 1.5V	2N5880, 2N5882	I _{CEX}	-	0.5	mA
$V_{CE} = 60V$, $V_{BE(off)} = 1.5V$, $T_{C} = 150$ °C	2N5879, 2N5881		-	5.0	
$V_{CE} = 80V$, $V_{BE(off)} = 1.5V$, $T_{C} = 150$ °C	2N5880, 2N5882		-	5.0	
Collector Cutoff Current					
V _{CE} = 60V, I _E = 1.5V	2N5879, 2N5881	I _{CBO}	-	0.5	mA
V _{CE} = 80V, I _E = 1.5V	2N5880, 2N5882		-	0.5	
Emitter Cutoff Current					
$V_{EB} = 5.0V$, $I_C = 0$		I _{EBO}	-	1.0	mA
DC Current Gain ⁽¹⁾					
$I_C = 2A$, $V_{CE} = 4V$		h _{FE}	35	-	-
$I_C = 6A$, $V_{CE} = 4V$			20	100	
$I_C = 15A$, $V_{CE} = 4V$			4.0	-	
Collector-Emitter Saturation Voltage(1)					
$I_C = 7A$, $I_B = 0.7A$		$V_{CE(sat)}$	-	1.0	V
$I_C = 15A$, $I_B = 3.75A$			-	4.0	
Base-Emitter Saturation Voltage(1)		$V_{BE(sat)}$			V
I _C = 15A, I _B = 3.75A	I _C = 15A, I _B = 3.75A		-	2.5	v l



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ELECTRICAL CHARACTERISTICS @ 25°C unless otherwise noted

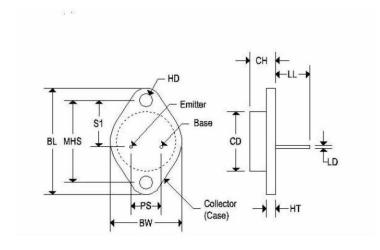
Characteristics		Symbol	Min	Max	Unit	
Base-Emitter On-Voltage $V_{CE} = 4.0V$, $I_C = 6.0A$		V _{BE(ON)}	-	1.5	V	
Current Gain – Bandwidth Product ⁽²⁾ I _C = 1.0A, V _{CE} = 10V, f _{test} = 1.0MHz		f⊤	4.0	-	MHz	
Output Capacitance 2N5879, 2N5881 VCB = 10V, IE = 0, f = 100kHz 2N5880, 2N5882		C _{ob}	-	600 400	Pf	
Small Signal Current Gain $I_C = 2A$, $V_{CE} = 4.0V$, $f = 1KHz$		h _{fe}	20	-	-	
Rise Time			t _r	-	0.7	μs
Storage Time $V_{CC} = 30V$, $I_C = 6.0A$, $I_{B1} = I_{B2} = 0.6A$ Fall Time		ts	-	1.0	μs	
		t _f	-	0.8	μs	

Note 1: Pulse width = 350µs, duty cycle ≤ 0.02

Note 2: $f_T = |h_{fe}| \circ f_{test}$

MECHANICAL CHARACTERISTICS

Case	TO-3
Marking	Alpha-numeric
Pin out	See below



	TO-3				
	Inches		Millin	neters	
	Min Max		Min	Max	
CD	-	0.875	-	22.220	
CH	0.250	0.380	6.860	9.650	
HT	0.060	0.135	1.520	3.430	
BW		1.050	•	26.670	
HD	0.131	0.188	3.330	4.780	
LD	0.038	0.043	0.970	1.090	
LL	0.312	0.500	7.920	12.700	
BL	1.550 REF		REF 39.370 REF		
MHS	1.177	1.197	29.900	30.400	
PS	0.420	0.440	10.670	11.180	
S1	0.655	0.675	16.640	17.150	



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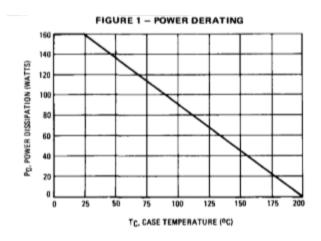


FIGURE 2 - SWITCHING TIMES TEST CIRCUIT

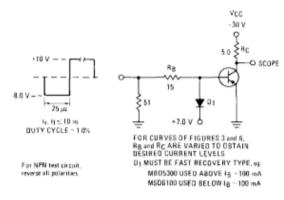


FIGURE 3 - TURN-ON TIME

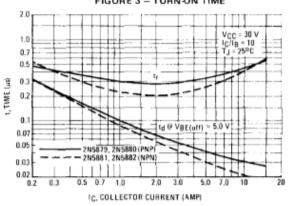
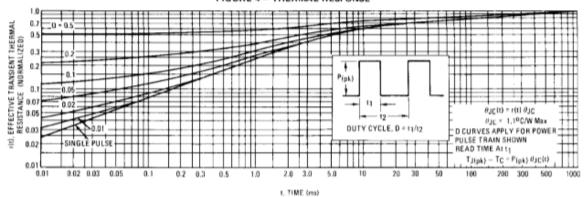


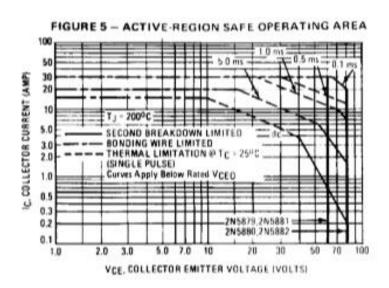
FIGURE 4 - THERMAL RESPONSE

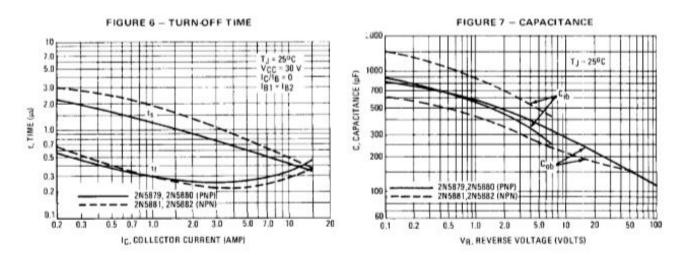




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